

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is provided, in which an optical axis of a far-field pattern (FFP) is stabilized and which is capable of oscillating in a fundamental transverse mode up to a high output. An optical pickup
5 apparatus also is provided, in which an optical axis of an FFP is stabilized and which is capable of being operated in fundamental transverse mode oscillation up to a high output. A semiconductor laser device is formed on a tilted substrate composed of a compound semiconductor, and includes an active layer and two cladding layers interposing the active layer
10 therebetween. One of the cladding layers forms a mesa-shaped ridge. The ridge includes a first region where a width of a bottom portion of the ridge is substantially constant and a second region where the width of the bottom portion of the ridge is varied continuously. The second region is placed between the first region and an end face in an optical path.